

## PNP HIGH POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/379

### Devices

2N3791

2N3792

### Qualified Level

JAN  
JANTX  
JANTXV

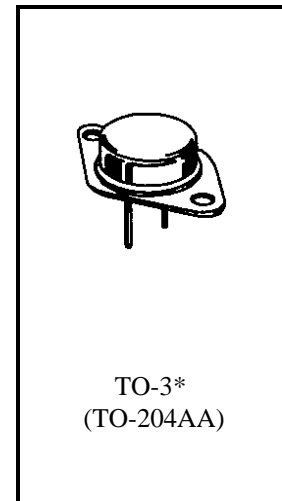
### MAXIMUM RATINGS

Ratings	Symbol	2N3791	2N3792	Unit
Collector-Emitter Voltage	$V_{CEO}$	60	80	Vdc
Collector-Base Voltage	$V_{CBO}$	60	80	Vdc
Emitter-Base Voltage	$V_{EBO}$	7.0		Vdc
Base Current	$I_B$	4.0		Adc
Collector Current	$I_C$	10		Adc
Total Power Dissipation	@ $T_A = +25^{\circ}\text{C}$ <sup>(1)</sup>	5.0		W
	@ $T_C = +100^{\circ}\text{C}$ <sup>(2)</sup>	85.7		W
Operating & Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200		$^{\circ}\text{C}$

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.17	$^{\circ}\text{C}/\text{W}$

- Derate linearly @  $28.57 \text{ mW}/^{\circ}\text{C}$  for  $T_A > +25^{\circ}\text{C}$
- Derate linearly @  $0.857 \text{ mW}/^{\circ}\text{C}$  for  $T_C > +100^{\circ}\text{C}$



\*See Appendix A for Package Outline

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$	2N3791 2N3792	$V_{(BR)CEO}$	60 80	Vdc
Collector-Emitter Cutoff Current $V_{CE} = 50 \text{ Vdc}$ $V_{CE} = 70 \text{ Vdc}$	2N3791 2N3792	$I_{CES}$	5.0 5.0	mAdc
Collector-Emitter Cutoff Current $V_{CE} = 60 \text{ Vdc}, V_{BE} = 1.5 \text{ Vdc}$ $V_{CE} = 80 \text{ Vdc}, V_{BE} = 1.5 \text{ Vdc}$	2N3791 2N3792	$I_{CEX}$	5.0 5.0	mAdc

**ELECTRICAL CHARACTERISTICS (con't)**

Characteristics	Symbol	Min.	Max.	Unit
Collector-Base Cutoff Current V <sub>CB</sub> = 60 Vdc V <sub>CB</sub> = 80 Vdc	I <sub>CBO</sub>		5.0 5.0	mAdc
Emitter-Base Cutoff Current V <sub>EB</sub> = 7.0 Vdc	I <sub>EBO</sub>		5.0	mAdc

**ON CHARACTERISTICS <sup>(3)</sup>**

Forward-Current Transfer Ratio I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 2.0 Vdc I <sub>C</sub> = 3.0 Adc, V <sub>CE</sub> = 2.0 Vdc I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 2.0 Vdc I <sub>C</sub> = 10 Adc, V <sub>CE</sub> = 4.0 Vdc	h <sub>FE</sub>	50 30 10 5.0	150 120	
Collector-Emitter Saturation Voltage I <sub>C</sub> = 5.0 Adc, I <sub>B</sub> = 0.5 Adc I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 2.0 Adc	V <sub>CE(sat)</sub>		1.0 2.5	Vdc
Base-Emitter Saturation Voltage I <sub>C</sub> = 5.0 Adc, I <sub>B</sub> = 0.5 Adc I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 2.0 Adc	V <sub>BE(sat)</sub>		1.5 3.0	Vdc

**DYNAMIC CHARACTERISTICS**

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 MHz	h <sub>fe</sub>	4.0	20	
Small-Signal Short-Circuit Forward Current Transfer Ratio I <sub>C</sub> = 0.5 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz	h <sub>fe</sub>	30	300	
Output Capacitance V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz	C <sub>obo</sub>		500	pF

**SAFE OPERATING AREA**

<b>DC Tests</b>				
T <sub>C</sub> = +25°C, 1 Cycle, t ≥ 1.0 s				
<b>Test 1</b>				
V <sub>CE</sub> = 15 Vdc, I <sub>C</sub> = 10 Adc				
<b>Test 2</b>				
V <sub>CE</sub> = 40 Vdc, I <sub>C</sub> = 3.75 Adc				
<b>Test 3</b>				
V <sub>CE</sub> = 55 Vdc, I <sub>C</sub> = 0.9 Adc	2N3791			
V <sub>CE</sub> = 65 Vdc, I <sub>C</sub> = 0.9 Adc	2N3792			

(3) Pulse Test: Pulse Width = 300µs, Duty Cycle ≤ 2.0%.

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Datasheets for electronics components.